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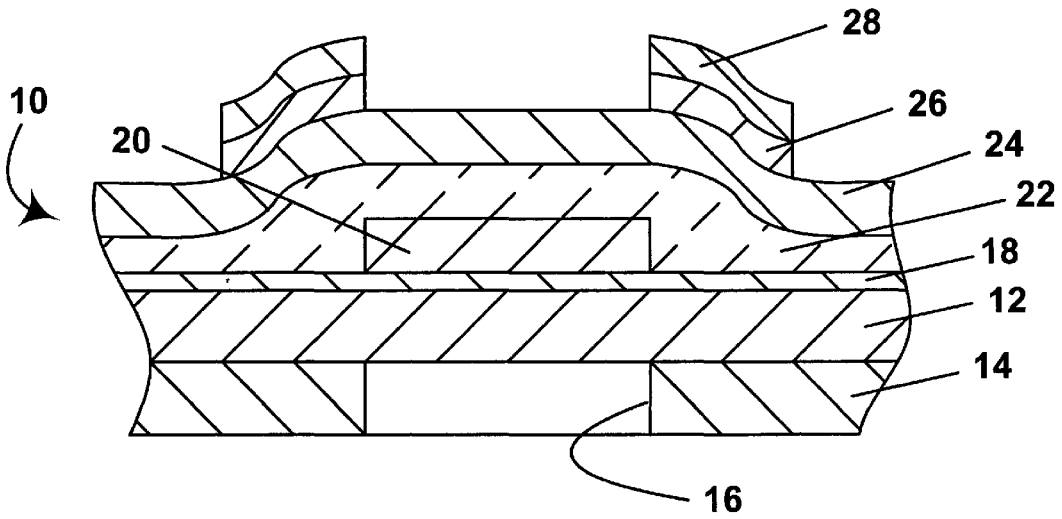
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(54) Title: PROCESS FOR FABRICATING THIN FILM TRANSISTORS



(57) Abstract: Transistors are formed by depositing at least one layer of semiconductor material on a substrate comprising a polyphenylene polyimide. The substrate permits the use of processing temperatures in excess of 300 °C during the processes used to form the transistor, thus allowing the formation of high quality silicon semiconductor layers. The substrate also has a low coefficient of thermal expansion, which closely matches that of silicon, thus reducing any tendency for a silicon layer to crack or delaminate.

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